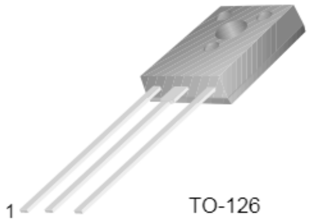
FAIRCHILD
SEMICONDUCTOR™

KSE340

High Voltage General Purpose Applications

- High Collector-Emitter Breakdown Voltage
- Suitable for Transformer
- Complement to KSE350



TO-126

1. Emitter 2.Collector 3.Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	500	mA
P_C	Collector Dissipation (T_C=25°C)	20	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 65 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 1mA, I_B = 0	300		V
I_{CBO}	Collector Cut-off Current	V_{CB} = 300V, I_E =0		100	∝A
I_{EBO}	Emitter Cut-off Current	V_{BE} = 3V, I_C = 0		100	∝A
h_{FE}	DC Current Gain	V_{CE} = 10V, I_C = 50mA	30	240	

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